

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	71588	semiconductor adj energy adj laboratory.as. or yamazaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:32
L2	16642	((photoresist resist mask pattern) and (remove etch etching removing) and conductive).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 11:42
L3	221	L1 and L2	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:32
L4	799	silicon adj nitride same hard adj mask same gate	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:41
L5	2	L3 and L4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:33
L6	232	4 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:34
L7	232	4 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:40
L8	3	1 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:40
L9	3133	silicon adj nitride same hard adj mask	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:56
L10	5	1 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:42
L11	343	9 and MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:43
L12	686	silicon adj nitride near5 hard adj mask	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:56

L13	0	12 and mosfett	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:56
L14	102	12 and mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:59
L15	1	("5863820").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 11:04
L16	1	("5814529").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 11:35
L17	1	("6303982").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 11:35
L18	457	photoresist same (remove etch etching removing) same (metal wiring wire conductive conductor) and @py<"1970"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 11:44
S1	1443	((gate electrode) and (resist photoresist) and (etch etching removing) and conductive).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:31
S2	71576	semiconductor adj energy adj laboratory.as. or yamazaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:05
S3	2	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:09
S4	127	semiconductor adj region.clm. and S2	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:22
S5	65938	Ishikawa.in.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:30
S6	2	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:22

S7	402	S2 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:30
S8	1	S4 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:31
S9	0	S1 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:31
S10	4639	((photoresist) and (etch etching removing) and conductive).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:32
S11	0	S7 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:32
S12	16627	((photoresist resist mask pattern) and (remove etch etching removing) and conductive).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 12:33
S13	9	S7 and S12	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 13:33
S14	221	S2 and S12	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/13 08:32
S15	18	"5814529"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 17:12
S16	319897	(pattern resist photoresist) same (metal conducting conductor)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 16:23
S17	186	S14 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 16:23
S18	2	("3,189,973").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 18:31

S19	1	("20040023448").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 18:36
S20	798	silicon adj nitride same hard adj mask same gate	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 18:38
S21	3	S2 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/12/12 18:37

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